

- CONFIDENTIAL**

10. The high-power semiconductor module as claimed in one of claims 1 to 9, characterized in that an electrically insulating housing (12) is arranged between the base plate (11) and the cover plate (13), and encloses the semiconductor chips (14) and the associated contact devices (15, 16).

11. The high-power semiconductor module as claimed in one of claims 1 to 10, characterized in that the semiconductor chips (14) are connected electrically in parallel within the high-power semiconductor module (10).

12. The high-power semiconductor module as claimed in claim 11, characterized in that at least some of the semiconductor chips (14) are controllable semiconductor switches, in particular IGBTs.

13. Use of a high-power semiconductor module as claimed in one of claims 1 to 12 in a power-electronics system, in which the high-power semiconductor module (10) is arranged together with a cooling apparatus (24), which is adjacent to the outer face of the base plate (11), to form a stack, and pressure is applied to it in the stack.

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